## Designer's™ Data Sheet

# **Insulated Gate Bipolar Transistor**

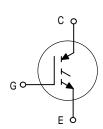
## N-Channel Enhancement-Mode Silicon Gate

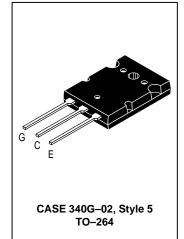
This Insulated Gate Bipolar Transistor (IGBT) uses an advanced termination scheme to provide an enhanced and reliable high voltage blocking capability. Short circuit rated IGBT's are specifically suited for applications requiring a guaranteed short circuit withstand time such as Motor Control Drives. Fast switching characteristics result in efficient operation at high frequencies.

- Industry Standard High Power TO–264 Package (TO–3PBL)
- High Speed Eoff: 70 μJ/A typical at 125°C
- High Short Circuit Capability 10 μs minimum
- Robust High Voltage Termination
- Robust RBSOA



IGBT IN TO-264 40 A @ 90°C 66 A @ 25°C **600 VOLTS SHORT CIRCUIT RATED** 





#### **MAXIMUM RATINGS** (T<sub>.1</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCES	600	Vdc
Collector–Gate Voltage (R <sub>GE</sub> = 1.0 MΩ)	VCGR	600	Vdc
Gate-Emitter Voltage — Continuous	VGE	±20	Vdc
Collector Current — Continuous @ T <sub>C</sub> = 25°C — Continuous @ T <sub>C</sub> = 90°C — Repetitive Pulsed Current (1)	IC25 IC90 ICM	66 40 132	Adc Apk
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	260 2.08	Watts W/°C
Operating and Storage Junction Temperature Range	TJ, T <sub>stg</sub>	-55 to 150	°C
Short Circuit Withstand Time (V <sub>CC</sub> = 360 Vdc, V <sub>GE</sub> = 15 Vdc, R <sub>G</sub> = 20 $\Omega$ )	t <sub>SC</sub>	10	μs
Thermal Resistance — Junction to Case – IGBT — Junction to Ambient	R <sub>θ</sub> JC R <sub>θ</sub> JA	0.48 35	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	TL	260	°C
Mounting Torque, 6–32 or M3 screw	10 lbf•in (1.13 N•m)		

<sup>(1)</sup> Pulse width is limited by maximum junction temperature.

Designer's Data for "Worst Case" Conditions — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. SOA Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

Preferred devices are Motorola recommended choices for future use and best overall value

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Ch	aracteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS				•		
Collector–to–Emitter Breakdown Voltage (VGE = 0 Vdc, I <sub>C</sub> = 250 μAdc) Temperature Coefficient (Positive)		V(BR)CES	600 —	 870	_	Vdc mV/°C
Emitter–to–Collector Breakdown Voltage (V <sub>GE</sub> = 0 Vdc, I <sub>EC</sub> = 100 mAdc)		V(BR)ECS	25	_	_	Vdc
Zero Gate Voltage Collector Current  (VCE = 600 Vdc, VGE = 0 Vdc)  (VCE = 600 Vdc, VGE = 0 Vdc, TJ = 125°C)		ICES	_	=	100 2500	μAdc
Gate–Body Leakage Current ( $V_{GE} = \pm 20 \text{ Vdc}$ , $V_{CE} = 0 \text{ Vdc}$ )		IGES	_	_	250	nAdc
ON CHARACTERISTICS (1)						
Collector-to-Emitter On-State Vo (VGE = 15 Vdc, IC = 20 Adc) (VGE = 15 Vdc, IC = 20 Adc, T (VGE = 15 Vdc, IC = 40 Adc)		VCE(on)	_ _ _	2.20 2.10 2.60	2.80 — 3.25	Vdc
Gate Threshold Voltage (V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 1 mAdc) Threshold Temperature Coeffici	ent (Negative)	VGE(th)	4.0 —	6.0 10	8.0 —	Vdc mV/°C
Forward Transconductance (V <sub>CE</sub> = 10 Vdc, I <sub>C</sub> = 40 Adc)		9fe	_	12	_	Mhos
DYNAMIC CHARACTERISTICS				_		
Input Capacitance	(V <sub>CE</sub> = 25 Vdc, V <sub>GE</sub> = 0 Vdc, f = 1.0 MHz)	C <sub>ies</sub>	_	6810	_	pF
Output Capacitance		C <sub>oes</sub>	_	464	_	
Transfer Capacitance	,	C <sub>res</sub>	_	15	_	
SWITCHING CHARACTERISTICS	(1)					
Turn-On Delay Time		<sup>t</sup> d(on)	_	126	_	ns
Rise Time	$(V_{CC}=360~Vdc,~I_{C}=40~Adc,~V_{GE}=15~Vdc,~L=300~\mu H$ $R_{G}=20~\Omega)$ Energy losses include "tail"	t <sub>r</sub>	_	95	_	
Turn-Off Delay Time		<sup>t</sup> d(off)	_	530	_	
Fall Time		t <sub>f</sub>	_	180	_	
Turn-Off Switching Loss		E <sub>off</sub>	_	1.50	2.10	mJ
Turn-On Delay Time	$(V_{CC}=360~Vdc,~I_{C}=40~Adc,~V_{GE}=15~Vdc,~L=300~\mu H~R_{G}=20~\Omega,~T_{J}=125°C)$ Energy losses include "tail"	td(on)	_	113	_	ns
Rise Time		t <sub>r</sub>	_	104	_	]
Turn-Off Delay Time		<sup>t</sup> d(off)	_	588	_	
Fall Time		t <sub>f</sub>	_	346	_	
Turn-Off Switching Loss		E <sub>off</sub>	_	2.70	_	mJ
Gate Charge		QT	_	248	_	nC
	$(V_{CC} = 360 \text{ Vdc}, I_{C} = 40 \text{ Adc}, V_{GE} = 15 \text{ Vdc})$	Q <sub>1</sub>	_	49	_	
		Q <sub>2</sub>	_	81	_	
INTERNAL PACKAGE INDUCTAN	CE	•	-	•	-	-
Internal Emitter Inductance (Measured from the emitter lead 0.25" from package to emitter bond pad)		LE	_	13	_	nH

<sup>(1)</sup> Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

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### TYPICAL ELECTRICAL CHARACTERISTICS

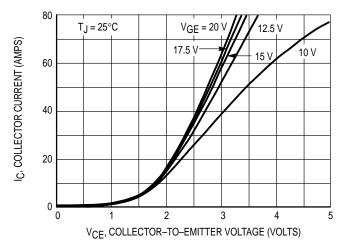


Figure 1. Output Characteristics

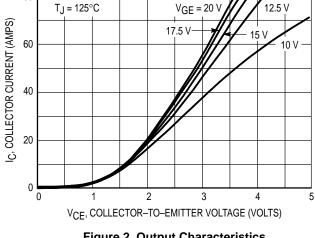


Figure 2. Output Characteristics

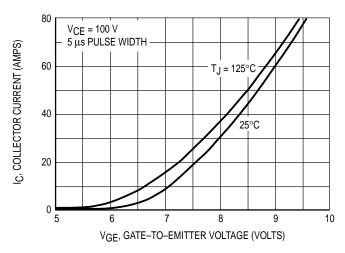


Figure 3. Transfer Characteristics

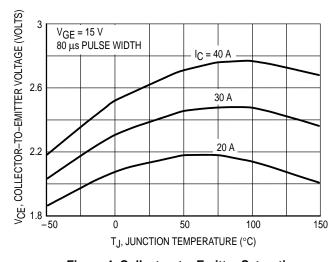


Figure 4. Collector-to-Emitter Saturation Voltage versus Junction Temperature

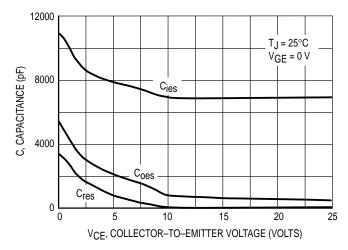


Figure 5. Capacitance Variation

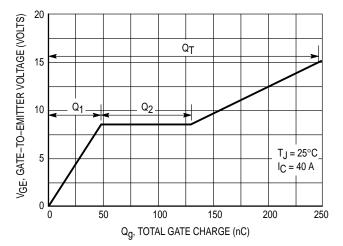


Figure 6. Gate-to-Emitter Voltage versus **Total Charge** 

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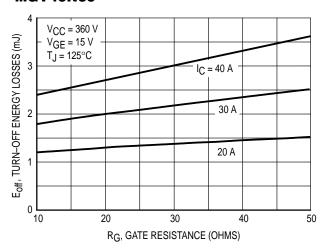


Figure 7. Turn–Off Losses versus
Gate Resistance

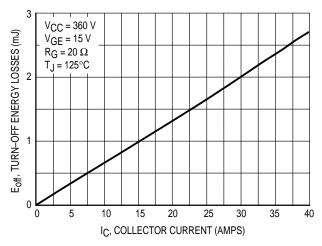


Figure 9. Turn-Off Losses versus Collector Current

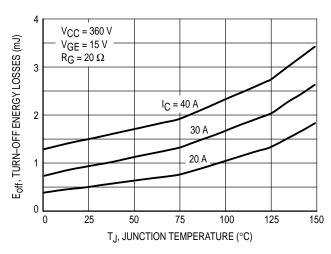


Figure 8. Turn-Off Losses versus Junction Temperature

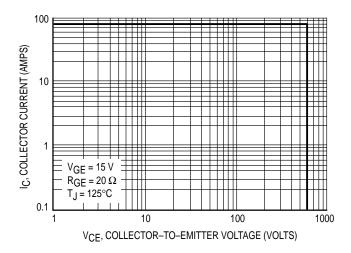
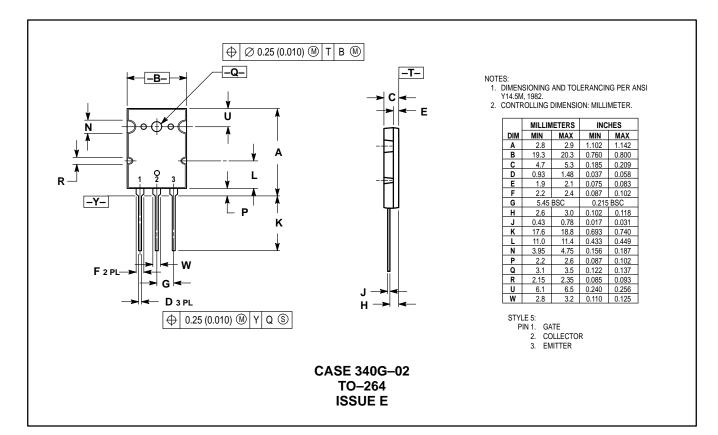


Figure 10. Reverse Biased Safe Operating Area

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### **PACKAGE DIMENSIONS**



#### **MGY40N60**

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